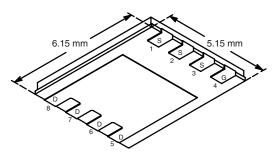




## P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY						
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)			
- 30	0.0065 at V <sub>GS</sub> = - 10 V	- 35	100 nC			

#### PowerPAK SO-8



**Bottom View** 

Ordering Information: Si7447ADP-T1-E3 (Lead (Pb)-free)

Si7447ADP-T1-GE3 (Lead (Pb)-free and Halogen-free)

#### **FEATURES**

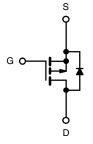
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET<sup>®</sup> Power MOSFET
- New Low Thermal Resistance PowerPAK<sup>®</sup> Package with Low 1.07 mm Profile
- 100 % R<sub>a</sub> Tested



ROHS COMPLIANT HALOGEN FREE

#### **APPLICATIONS**

- · Battery and Load Switching
  - Notebook Computers
  - Notebook Battery Packs



P-Channel MOSFET

Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V <sub>DS</sub>	- 30	V		
Gate-Source Voltage	V <sub>GS</sub>	± 25	v		
	T <sub>C</sub> = 25 °C		- 35		
Continuous Drain Current (T = 150 °C)	T <sub>C</sub> = 70 °C	L	- 28		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>A</sub> = 25 °C	I <sub>D</sub>	- 21.5 <sup>b, c</sup>		
	T <sub>A</sub> = 70 °C		- 17 <sup>b, c</sup>	A	
Pulsed Drain Current		I <sub>DM</sub>	- 60	A	
Continuous Source-Drain Diode Current	T <sub>C</sub> = 25 °C	la	- 28		
Continuous Source-Drain Diode Current	T <sub>A</sub> = 25 °C	I <sub>S</sub>	- 4.3 <sup>b, c</sup>		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	40		
Avalanche Energy	L = 0.1 mn	E <sub>AS</sub>	80	mJ	
	T <sub>C</sub> = 25 °C		83.3		
Manipular Davier Discipation	T <sub>C</sub> = 70 °C	В	53.3	107	
Maximum Power Dissipation	T <sub>A</sub> = 25 °C	P <sub>D</sub>	5.4 <sup>b, c</sup>	W	
	T <sub>A</sub> = 70 °C		3.4 <sup>b, c</sup>		
Operating Junction and Storage Temperature Ra	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	00		
Soldering Recommendations (Peak Temperature	-	260	°C		

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Typical	Maximum	Unit		
Maximum Junction-to-Ambient <sup>b, f</sup>	t ≤ 10 s	$R_{thJA}$	18	23	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R <sub>thJC</sub>	1.0	1.3	C/VV	

#### Notes:

- a. Based on  $T_C = 25$  °C.
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 10 s
- d. See Solder Profile (<a href="https://www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under Steady State conditions is 65 °C/W.

## Si7447ADP

## Vishay Siliconix



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 30			V
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I <sub>D</sub> = - 250 μA		- 33		mV/°C
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	,		5.3		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1	- 2.0	- 3	V
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 25 \text{ V}$			± 100	nA
Zoro Coto Voltago Drain Current	1	V <sub>DS</sub> = - 30 V, V <sub>GS</sub> = 0 V	- 30 V, V <sub>GS</sub> = 0 V			
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C		- 10	μΑ	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge -5 V, V_{GS} = -10 V$	- 30			Α
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 24 A		0.0054	0.0065	Ω
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 24 A		50		S
Dynamic <sup>b</sup>				•		
Input Capacitance	C <sub>iss</sub>			4650		pF
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		1200		
Reverse Transfer Capacitance	C <sub>rss</sub>			930		
Total Gate Charge	Qg			100	150	nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -24 \text{ A}$		15.5		
Gate-Drain Charge	$Q_{gd}$			25		
Gate Resistance	$R_{g}$	f = 1 MHz	1.7	3.5	5.3	Ω
Turn-On Delay Time	t <sub>d(on)</sub>			20	30	
Rise Time	t <sub>r</sub>	$V_{DD} = -15 \text{ V}, R_{L} = 1.5 \Omega$		25	40	ns
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong$ - 10 A, $V_{GEN}$ = - 10 V, $R_g$ = 1 $\Omega$		82	125	
Fall Time	t <sub>f</sub>			98	150	
Drain-Source Body Diode Characterist	tics					
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			- 28	A
Pulse Diode Forward Current <sup>a</sup>	I <sub>SM</sub>				- 60	
Body Diode Voltage	$V_{SD}$	I <sub>S</sub> = - 4.3 A		- 0.72	- 1.1	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>			47	70	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> = - 19 A, dl/dt = - 100 A/μs, T <sub>.I</sub> = 25 °C -		50	75	nC
Reverse Recovery Fall Time	t <sub>a</sub>	$_{\text{IF}} = -18 \text{ A}, \text{ al/at} = -100 \text{ A/}\mu\text{s}, \text{ I}_{\text{J}} = 25 ^{\text{1}}\text{C}$		22		
Reverse Recovery Rise Time t <sub>b</sub>						ns

#### Notes:

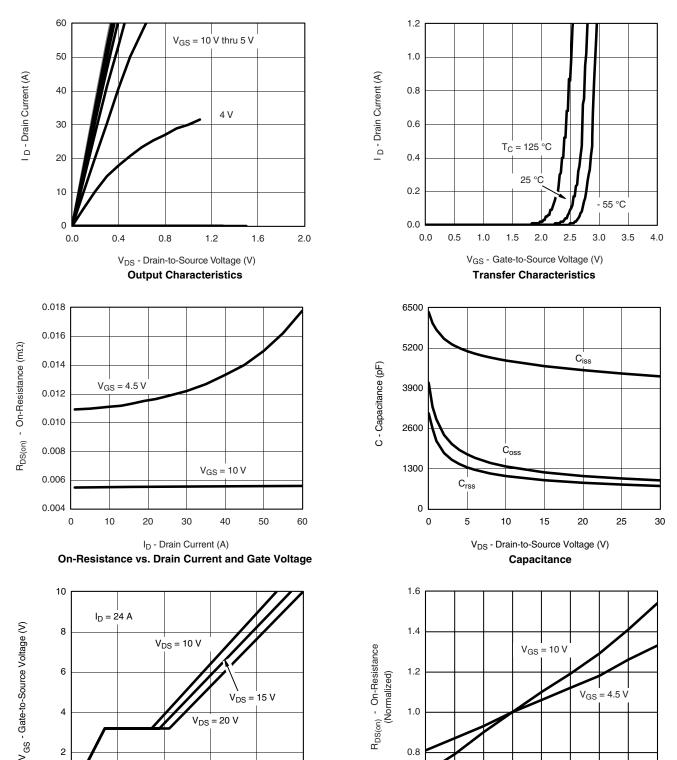
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.



#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



0.8

- 50

- 25

0

25

50

T<sub>J</sub> - Junction Temperature (°C)

On-Resistance vs. Junction Temperature

75

100

2

0

0

21

63

Q<sub>g</sub> - Total Gate Charge (nC)

**Gate Charge** 

84

105

42

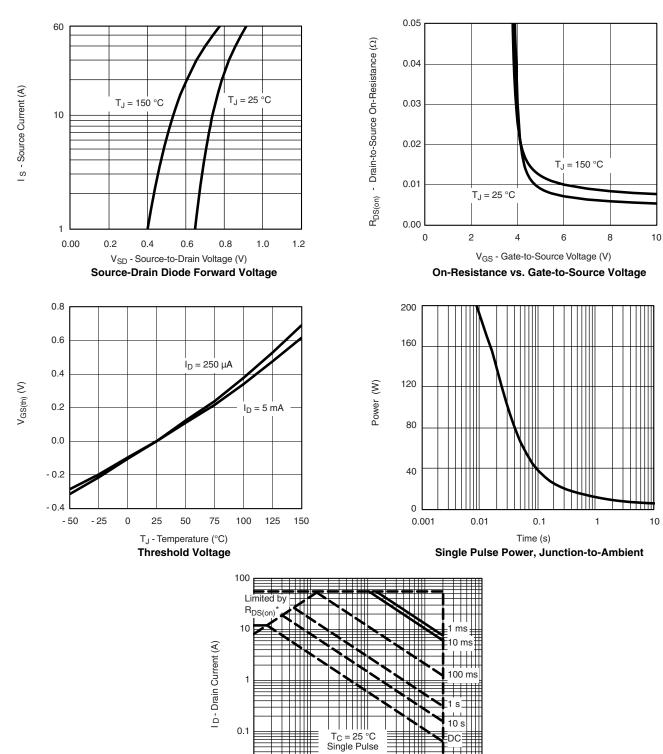
125

150

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#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



 $\label{eq:VDS} V_{DS} \text{ - Drain-to-Source Voltage (V)} \\ \text{* } V_{GS} > \text{minimum } V_{GS} \text{ at which } R_{DS(on)} \text{ is specified} \\ \textbf{Safe Operating Area, Junction-to-Ambient} \\$ 

0.1

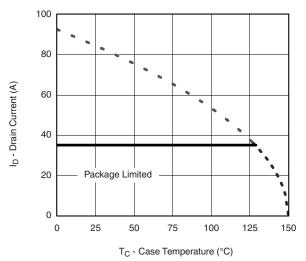
10

100

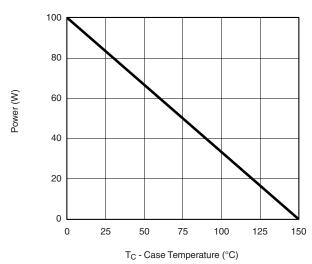
0.01 L 0.01

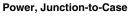


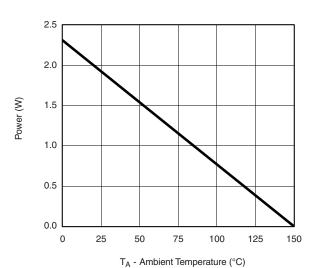
#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



#### **Current Derating\***







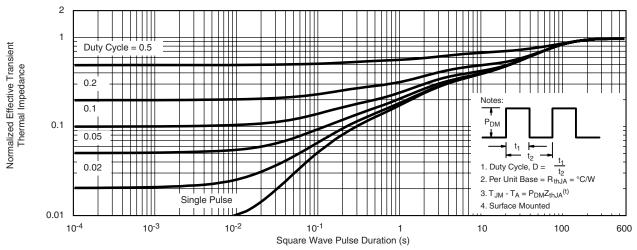
Power, Junction-to-Ambient

<sup>\*</sup> The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

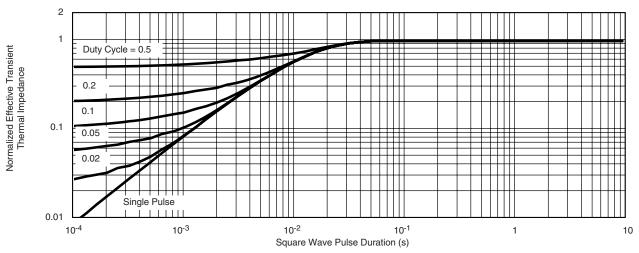
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#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



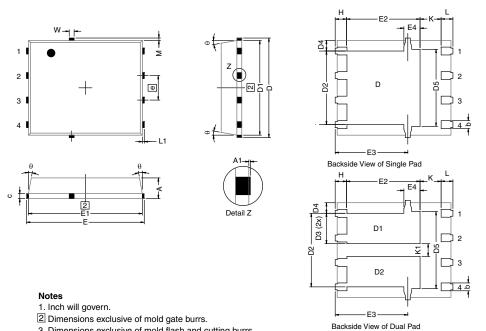
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg273358">www.vishay.com/ppg273358</a>.



DWG: 5881

## PowerPAK® SO-8, (Single/Dual)



	3. Dimensions exclusive	of mold flash and cuttin	g burrs.					
DIM.		MILLIMETERS			INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.		
A	0.97	1.04	1.12	0.038	0.041	0.044		
A1		-	0.05	0	-	0.002		
b	0.33	0.41	0.51	0.013	0.016	0.020		
С	0.23	0.28	0.33	0.009	0.011	0.013		
D	5.05	5.15	5.26	0.199	0.203	0.207		
	4.00	4.00	F 00	0.400	0.400	0.407		

Α	0.97	1.04	1.12	0.038	0.041	0.044	
A1		-	0.05	0	-	0.002	
b	0.33	0.41	0.51	0.013	0.016	0.020	
С	0.23	0.28	0.33	0.009	0.011	0.013	
D	5.05	5.15	5.26	0.199	0.203	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.56	3.76	3.91	0.140	0.148	0.154	
D3	1.32	1.50	1.68	0.052	0.059	0.066	
D4		0.57 typ.			0.0225 typ.		
D5		3.98 typ.		0.157 typ.			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	5.79	5.89	5.99	0.228	0.232	0.236	
E2 (for AL product)	3.30	3.48	3.66	0.130	0.137	0.144	
E2 (for other product)	3.48	3.66	3.84	0.137	0.144	0.151	
E3	3.68	3.78	3.91	0.145	0.149	0.154	
E4 (for AL product)		0.58 typ.			0.023 typ.		
E4 (for other product)		0.75 typ.			0.030 typ.		
е		1.27 BSC			0.050 BSC		
K (for AL product)		1.45 typ.		0.057 typ.			
K (for other product)		1.27 typ.			0.050 typ.		
K1	0.56	-	=	0.022	-	=	
Н	0.51	0.61	0.71	0.020	0.024	0.028	
L	0.51	0.61	0.71	0.020	0.024	0.028	
L1	0.06	0.13	0.20	0.002	0.005	0.008	
θ	0°	-	12°	0°	-	12°	
W	0.15	0.25	0.36	0.006	0.010	0.014	
M	0.125 typ.			0.005 typ.			
ECN: C13-0702-Rev. K, 20	)-May-13			•			

Revison: 20-May-13 Document Number: 71655



### RECOMMENDED MINIMUM PADS FOR PowerPAK® SO-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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Vishay

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Revision: 02-Oct-12 Document Number: 91000